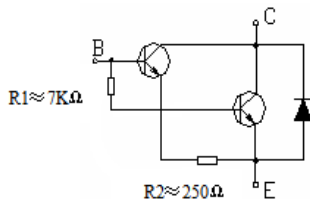
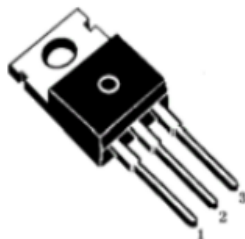


Marking code: TIP122 Silicon NPN triode 1: Base 2: Collector 3: Emitter

TO-220



FEATURES

- High current capability
- High switching speed
- Complementary to TIP127

Maximum ratings(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	100	V
Collector-Emitter Voltage	VCEO	100	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	5	A
Collector Power Dissipation	PC	65	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55~150	°C

Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Sustaining Voltage	V(BR)CEO	IC=0.1mA IB=0	100		V
Collector-Emitter Sustaining Voltage	V(BR)CEO	IC=10mA IB=0	100		V
Emitter-Base Breakdown Voltage	VEBO	IE=3mA IC=0	5		V
Collector Cutoff Current	ICBO	VCB=100V IE=0		0.2	mA
Collector Cutoff Current	ICEO	VCE=50V IB=0		0.5	mA
Emitter Cutoff Current	IEBO	VEB=5V IC=0		2	mA
DC Current Gain	hFE	VCE=3V IC=500mA	1000		
		VCE=5V IC=3A	1000	15000	
Collector-Emitter Saturation Voltage	VCE(sat)	IC=3A IB=12mA		2	V
		IC=5A IB=20mA		4	V
Collector-Base Saturation Voltage	VBE(sat)	IC=3A IB=12mA		2.5	V
Base-Emitter On Voltage	VBE(on)	VCE=3V IC=3A		2.5	V